



CST5N50 N-Ch 500V Fast Switching MOSFETs

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced VD MOSFETS

CST5N50 Product Summary



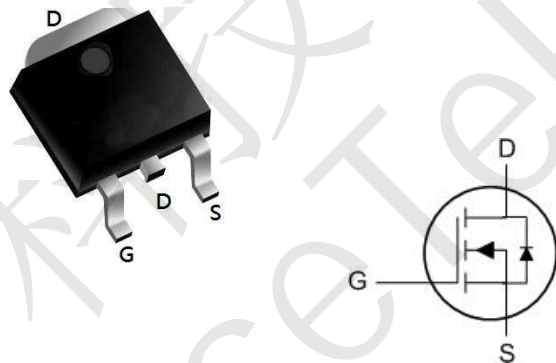
BVDSS	RDSON	ID
500V	1.45mΩ	5A

CST5N50 Description

The CST5N50 is the Advanced VD N-ch MOSFETS, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The CST5N50 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

CST5N50 TO252 Pin Configuration



CST5N50 Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V _{DSS}	Drain-Source Voltage	500	V
I _D	Drain Current - Continuous (TC= 25°C) - Continuous (TC= 100°C)	5	A
		2.6*	A
I _{DM}	Drain Current - Pulsed (Note 1)	20*	A
V _{GSS}	Gate-Source Voltage	± 30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	167	mJ
I _{AR}	Avalanche Current (Note 1)	5	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	10.6	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5	V/ns
P _D	Power Dissipation (TC = 25°C) - Derate above 25°C	24.5	W
		0.2	W/°C
T _j , T _{stg}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

Thermal Characteristics

Symbol	Parameter	Value	Units
R _{θJC}	Thermal Resistance, Junction-to-Case	4.20	°C/W
R _{θJS}	Thermal Resistance, Case-to-Sink Typ.	--	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	48.2	°C/W



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CST5N50 Electrical Characteristics TC = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	500			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.49		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500 V, V _{GS} = 0 V			1	μA
		V _{DS} = 400 V, TC = 125°C			10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Characteristics						
V _{GS(TH)}	Gate Threshold voltage	V _{DS} =V _{GS} , I _D =250 uA	2.0		4.0	V
R _{DS(On)}	Drain-Source on-state resistance	V _{GS} =10 V, I _D = 2A, T _J = 25°C		1.45	1.8	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 2.5 A (Note 4)		2.90		S
Dynamic Characteristics						
C _{iss}	Input capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz		415		pF
C _{oss}	Output capacitance			58		pF
C _{rss}	Reverse transfer capacitance			1.4		pF
Switching Characteristics						
t _{d(on)}	Turn On Delay Time	V _{DD} = 250 V, ID = 5 A, R _G = 25 Ω (Note 4, 5)		7		ns
t _r	Rising Time			22		ns
t _{d(off)}	Turn Off Delay Time			15		ns
t _f	Fall Time			23		ns
Q _g	Total Gate Charge	V _{DS} = 400 V, ID = 5 A, V _{GS} = 10 V (Note 4, 5)		13		nC
Q _{gs}	Gate-Source Charge			4.9		nC
Q _{gd}	Gate-Drain Charge			2.3		nC
Drain-source Diode Characteristics and Maximum Ratings						
I _S	Maximum continuous Drain-source Diode Forward Current				5	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				20	A
V _{SD}	Diode Forward Voltage	V _{GS} = 0 V, I _S = 5 A			1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 5 A, di _F / dt = 100 A/μs (Note 4)		289		ns
Q _{rr}	Reverse Recovery Charge			1.2		μC
Notes: 1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 10.6 mH, IAS = 5 A, VDD = 50V, RG = 25 Ω, Starting TJ = 25°C 3. ISD≤5A, di/dt ≤200A/us, VDD ≤ BVDSS, Starting TJ = 25°C 4. Pulse Test : Pulse width ≤ 300us, Duty cycle ≤ 2% 5. Essentially independent of operating temperature						



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CST5N50 Typical Characteristics

Table 7 Reverse diode characteristics

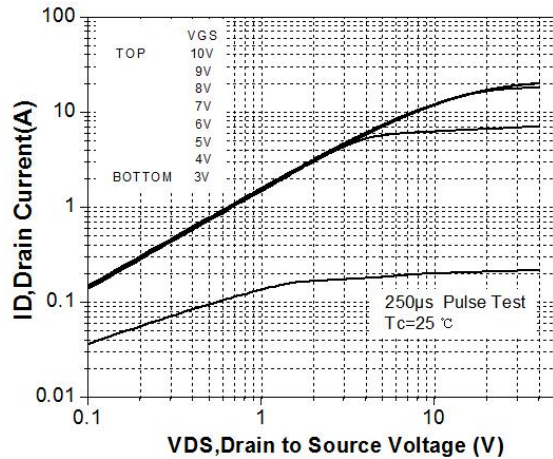


Figure 1. On-Region Characteristics

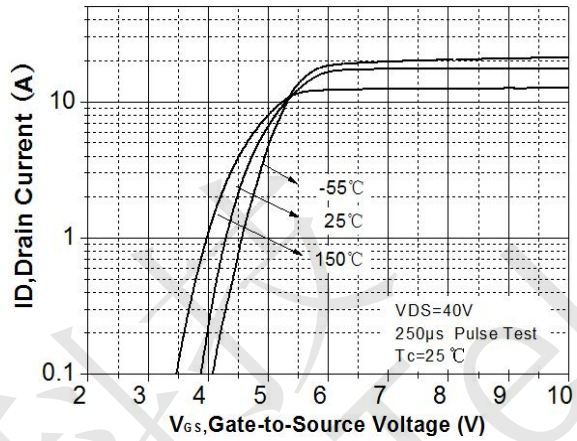


Figure 2. Transfer Characteristics

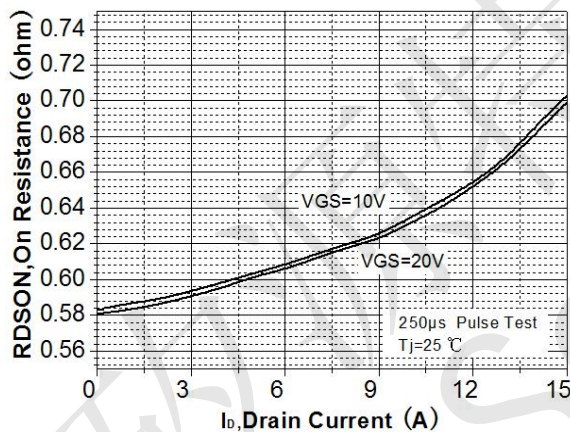


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

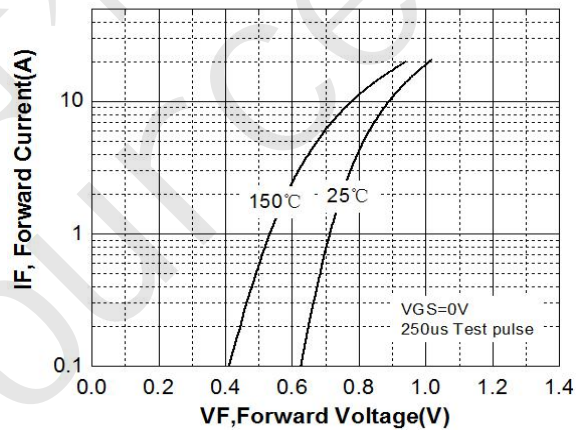


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

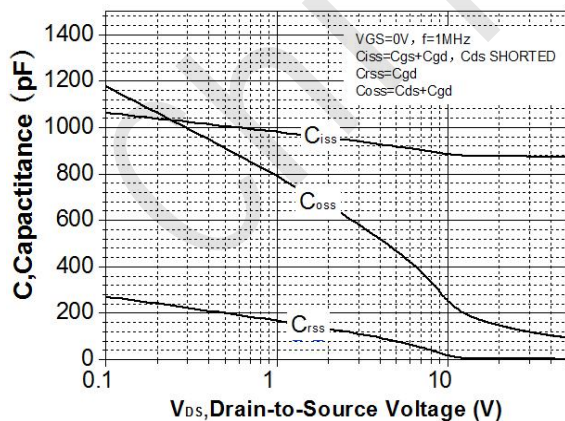


Figure 5. Capacitance Characteristics

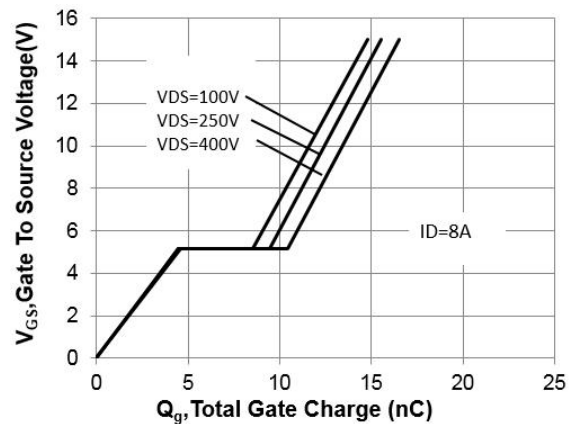


Figure 6. Gate Charge Characteristics



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CST5N50 Typical Characteristics (Continued)

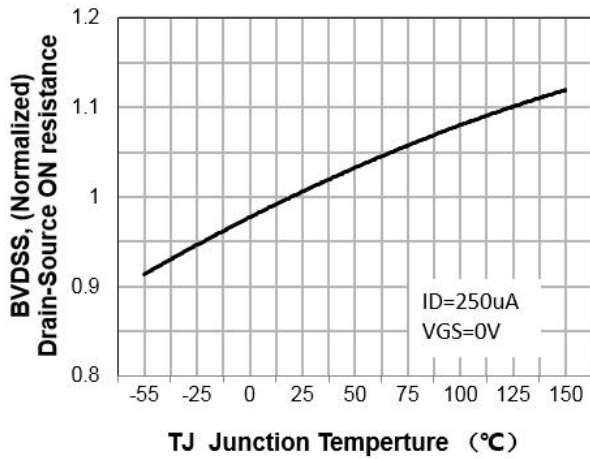


Figure 7. Breakdown Voltage Variation vs Temperature

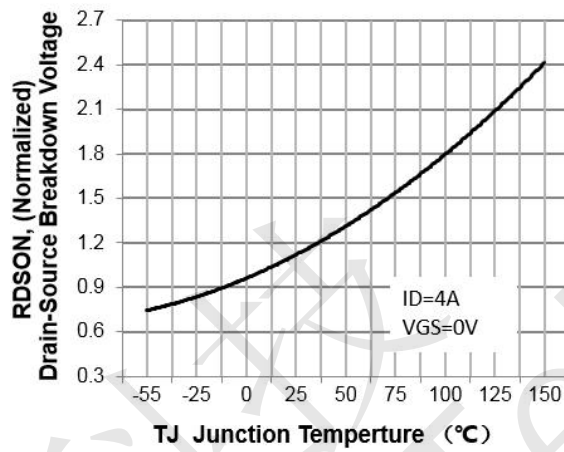


Figure 8. On-Resistance Variation vs Temperature

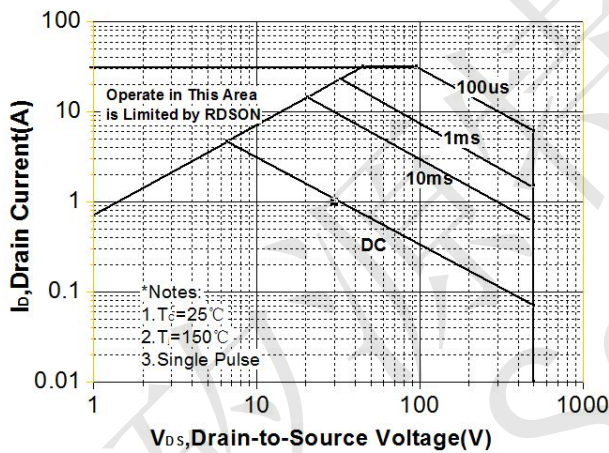


Figure 9. Maximum Safe Operating Area

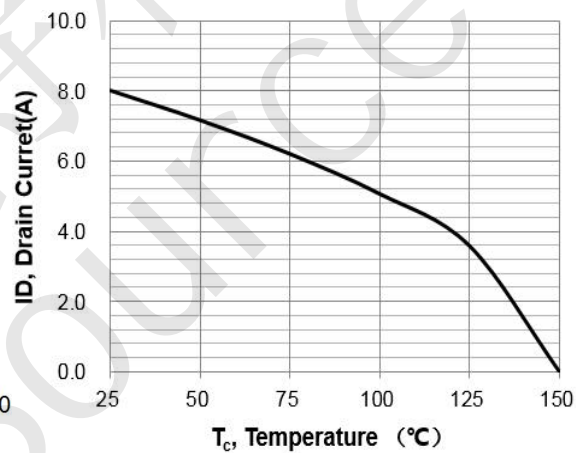


Figure 10. Maximum Drain Current vs Case Temperature

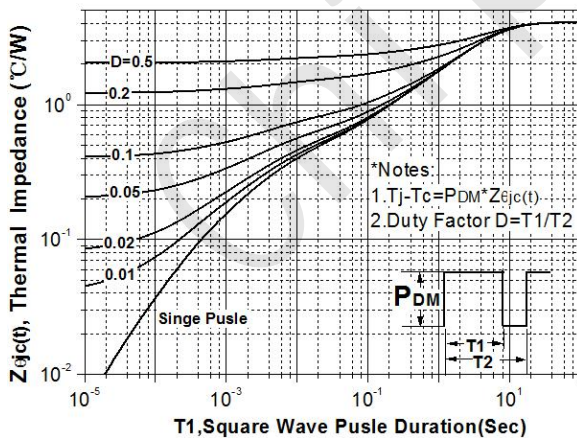
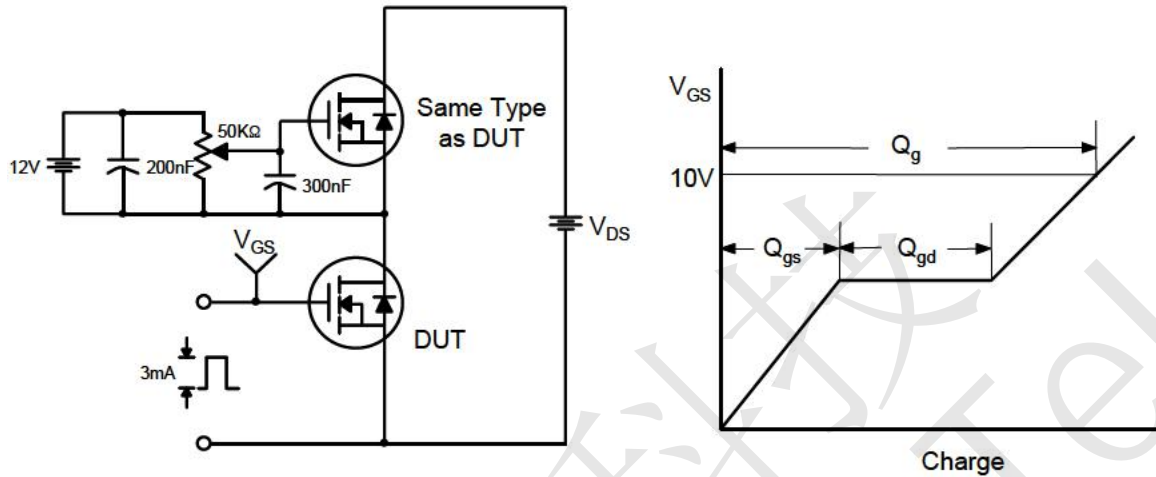


Figure 11. Transient Thermal Response Curve

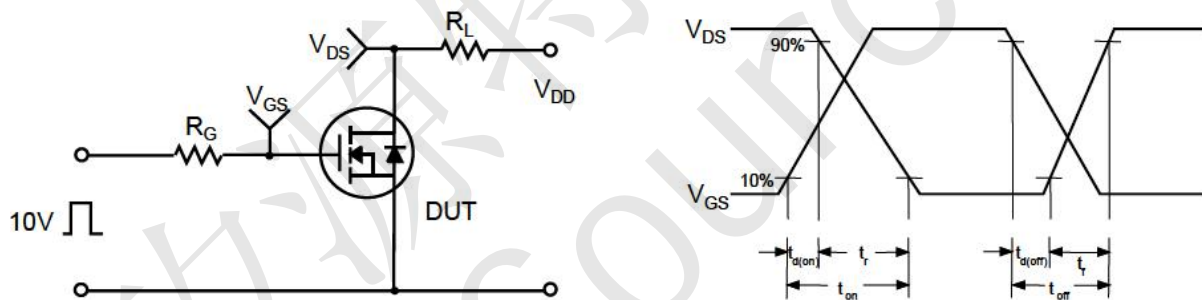


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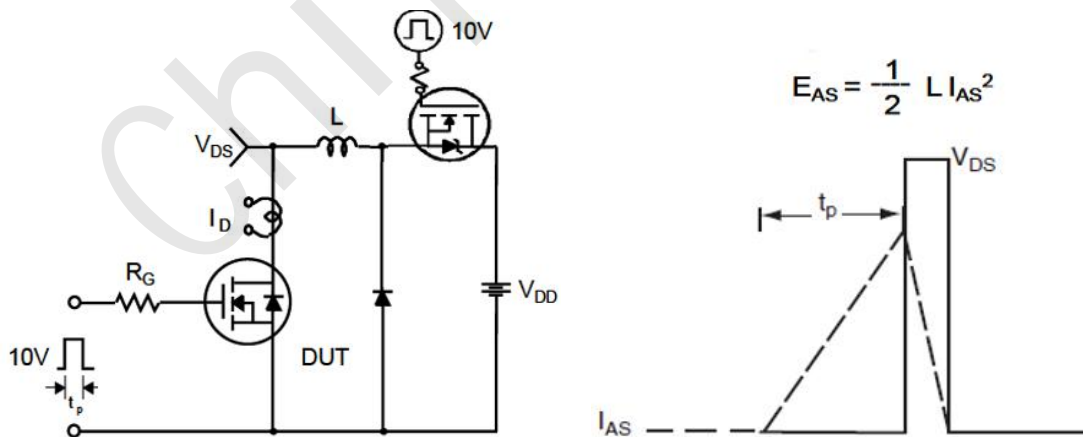
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



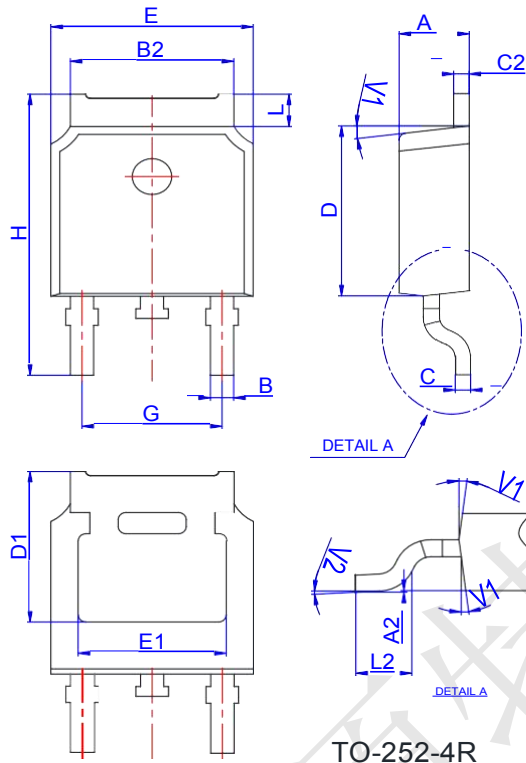
Unclamped Inductive Switching Test Circuit & Waveforms





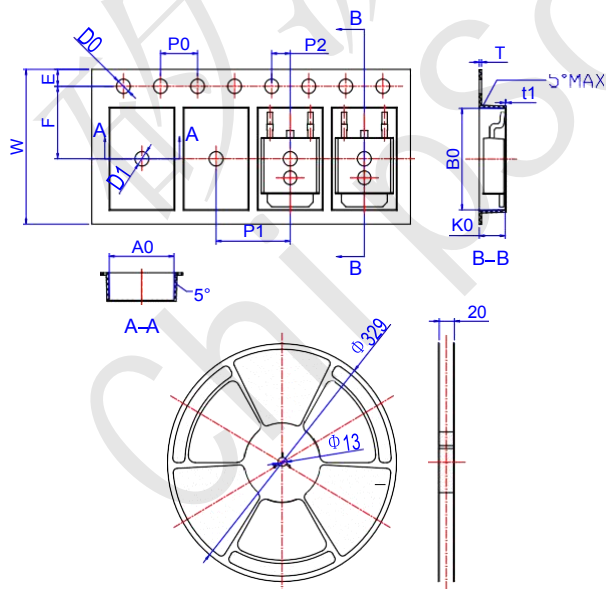
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CST5N50 Package Mechanical Data-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

CST5N50 Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583